

- GENERAL PURPOSE SILICON DIODES
- ALL JUNCTIONS COMPLETELY PROTECTED WITH SILICON DIOXIDE
- COMPATIBLE WITH ALL WIRE BONDING AND DIE ATTACH TECHNIQUES EXCEPT SOLDER REFLOW

**CD483B
CD485B
CD486B
CD645
AND
CD5194 thru CD5196**

MAXIMUM RATINGS

Operating Temperature: -65°C to +175°C

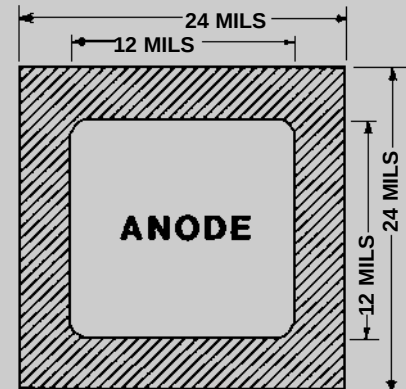
Storage Temperature: -65°C to +175°C

ELECTRICAL CHARACTERISTICS @ 25°C, unless otherwise specified

TYPE	V_{RM}	V_{RWM}	I_O	I_O $T_A = +150^\circ C$	I_{FSM} $t_p = 1/120 S$ $T_A = 25^\circ C$
	$V(pk)$	$V(pk)$	mA	mA	A
CD483B	80	70	200	50	2
CD485B	180	180	200	50	2
CD486B	250	225	200	50	2
CD645	270	225	400	150	5
CD5194	80	70	200	50	2
CD5195	180	180	200	50	2
CD5196	250	225	200	50	2

TYPE	$V_F(1)$	I_{R1} at V_{RWM} $T_A = 25^\circ C$	I_{R2} at V_{RM} $T_A = 25^\circ C$	I_{R3} at V_{RWM} $T_A = 150^\circ C$	CAP @ $V_R = 4V$
	V dc	nA dc	μA	μA dc	pF
CD483B	0.8 - 1.0	25	100	5	—
CD485B	0.8 - 1.0	25	100	5	—
CD486B	0.8 - 1.0	25	100	5	—
CD645	0.8 - 1.0	50	50	25	2.0
CD5194	0.8 - 1.0	25	100	5	—
CD5195	0.8 - 1.0	25	100	5	—
CD5196	0.8 - 1.0	25	100	5	—

NOTE 1 AT 100mA (pulsed) except for CD645 which is at 400mA (pulsed)



DESIGN DATA

METALLIZATION:

Top: (Anode).....Al
Back: (Cathode).....Au

AL THICKNESS25,000 Å Min

GOLD THICKNESS4,000 Å Min

CHIP THICKNESS10 Mils

TOLERANCES: ALL
Dimensions ± 2 mils



CD483B, CD485B, CD486B, CD645, CD5194 thru CD5196

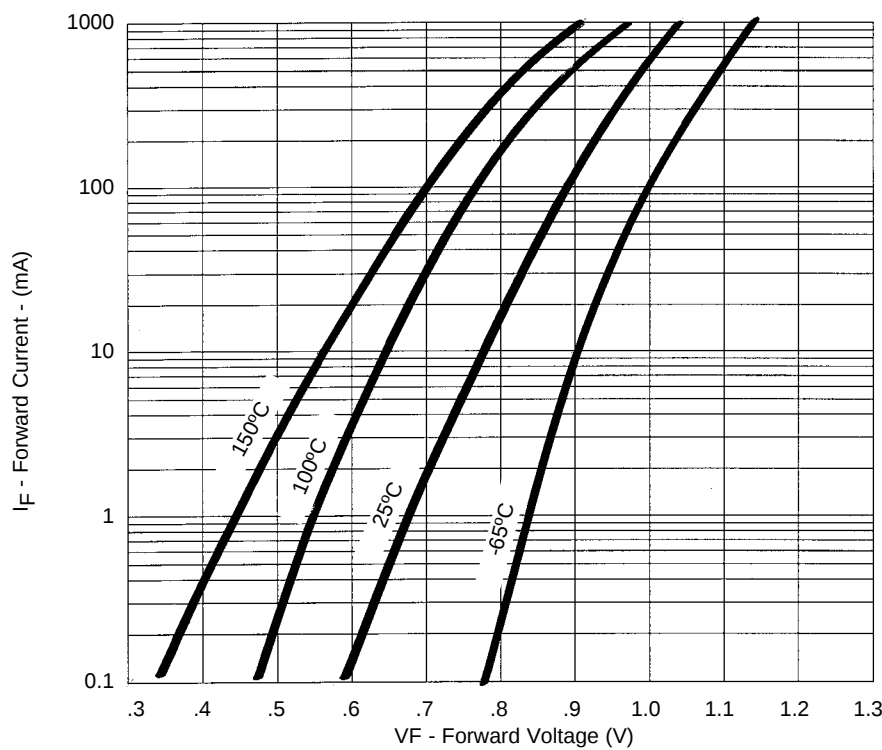
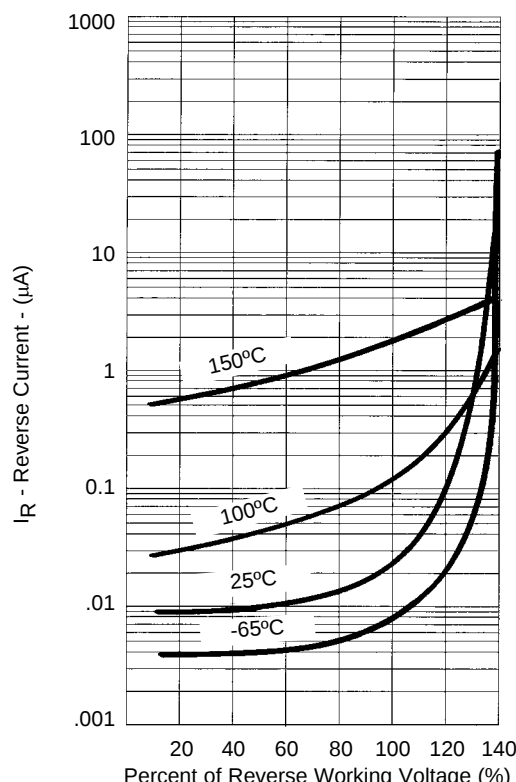


FIGURE 2
Typical Forward Current
vs Forward Voltage



NOTE : All temperatures shown on graphs are junction temperatures

FIGURE 3
Typical Reverse Current
vs Reverse Voltage